



Future Normal in Semiconductor

2025-02-14(금), 10:55-12:40

좌장: 추후업데이트 예정

D. Thin Film Process Technology 분과

[FE2-D] Thin Film Transistors - II

<p>FE2-D-1 10:55-11:10</p>	<p>A Study of CMOS Compatible Anti-Ambipolar Transistor based on Sputtered n-Type In-Based Oxide and p-Type Metalloid Channel Chanwoo Jung¹, Seok Hyun Hwang², and Jae Kyeong Jeong^{1,2} ¹Department of Display Science and Engineering, Hanyang University, ²Department of Electronic Engineering, Hanyang University,</p>
<p>FE2-D-2 11:10-11:25</p>	<p>Effect of Device Geometry Variation on Memory Performance of 2TOC DRAM Cells Using Double-Layered InGaZnO Active Channel Structures Sang Han Ko, Kyung Min Kim, and Sung Min Yoon Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</p>
<p>FE2-D-3 11:25-11:40</p>	<p>Influence of Oxygen Content in IGZO on the Memory Window of FeTFT He Young Kang, Seung Hee Cha, and Jae Kyeong Jeong Department of Electronic Engineering, Hanyang University</p>
<p>FE2-D-4 11:40-11:55</p>	<p>Reduction of Contact Resistance in MoS₂ Devices Using a Sb-Based Semimetal Contact Structure Ha Yeon Choi, Hye Seong Park, Joon Soo Byeon, Ju Yong Shin, Seung Ri Jeong, Shivam Kumar Gautam, and Hi-Deok Lee Department of Electronics Engineering, Chungnam National University</p>
<p>FE2-D-5 11:55-12:10</p>	<p>Enhancing Contact Properties of MoS₂ based FETs by Al₂O₃ Interlayer Engineering via Atomic layer deposition Jihoon Park, Hwi Yoon, Sanghun Lee, Seonyeong Park, Inkyu Sohn, and Hyungjun Kim School of Electrical and Electronic Engineering, Yonsei University</p>
<p>FE2-D-6 12:10-12:25</p>	<p>Atomic Layer Deposition of Semimetallic TiS₂ Contact Layer for Contact Resistance Engineering Minu Cho¹, Jeongwoo Seo¹, Hwi Yoon¹, Inkyu Sohn¹, Jun Hyung Lim², Yunyong Nam², and Hyungjun Kim¹ ¹School of Electrical and Electronic Engineering, Yonsei University, ²Samsung Display Co., Ltd</p>



제 32회 한국반도체학술대회

The 32nd Korean Conference on Semiconductors

2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

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FE2-D-7 12:25-12:40	<p>Ternary Logic Transistors Using Multi-Stacked 2DEG Channels in Ultrathin Al₂O₃/ZnO Heterostructures</p> <p>Ji Hyeon Choi¹, Tae Jun Seok¹, Sang June Kim¹, Tae Joo Park¹, Kyun Seong Dae², Jae Hyuck Jang², Deok-Yong Cho³, and Sang Woon Lee⁴</p> <p>¹Department of Materials Science and Chemical Engineering, Hanyang University, ²KBSI, ³Jeonbuk University, ⁴Ajou University</p>
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